

MOSFETs Silicon N-Channel MOS (U-MOSVII-H)

TPCA8065-H

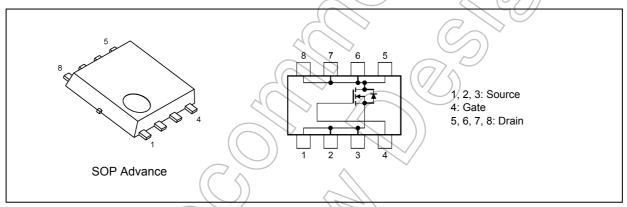
1. Applications

- High-Efficiency DC-DC Converters
- · Notebook PCs
- · Mobile Equipment

2. Features

- (1) Small footprint due to a small and thin package
- (2) High-speed switching
- (3) Small gate charge: $Q_{SW} = 4.3 \text{ nC}$ (typ.)
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 11.7 \text{ m}\Omega$ (typ.) ($V_{GS} = 4.5 \text{ V}$)
- (5) Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 30 \text{ V)}$
- (6) Enhancement mode: $V_{th} = 1.3 \text{ to } 2.3 \text{ V } (V_{DS} = 10 \text{ V}, I_D = 0.2 \text{ mA})$

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

Characteristics	(/)	Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	30	V
Gate-source voltage	>	V_{GSS}	±20	
Drain current (DC)	(Note 1)	Ι _D	16	Α
Drain current (pulsed)	(Note 1)	I _{DP}	48	
Power dissipation (T _c = 25 °C)		P_D	25	W
Power dissipation (t = 10 s)	(Note 2)	P_{D}	2.8	W
Power dissipation (t = 10 s)	(Note 3)	P _D	1.6	W
Single-pulse avalanche energy	(Note 4)	E _{AS}	66	mJ
Avalanche current		I _{AR}	16	Α
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



5. Thermal Characteristics

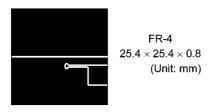
Characteristics				Max	Unit
Channel-to-case thermal resistance	$(T_c = 25 ^{\circ}C)$		R _{th(ch-c)}	5.0	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 2)	R _{th(ch-a)}	44.6	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 3)	R _{th(ch-a)}	78.1	°C/W

Note 1: Ensure that the channel temperature does not exceed 150 °C.

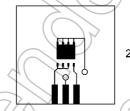
Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4: V_{DD} = 24 V, T_{ch} = 25 °C (initial), L = 0.2 mH, R_{G} = 1.2 Ω , I_{AR} = 16 A







 $\begin{aligned} & \text{FR-4} \\ 25.4 \times 25.4 \times 0.8 \\ & \text{(Unit: mm)} \end{aligned}$

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

Rev.4.0



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±0.1	μА
Drain cut-off current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	7	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	30	_	_	V
	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	15) b>	_	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.2 mA	1.3	<i>7</i> _	2.3	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 4.5 V, I _D = 8 A	/	11.7	14.5	mΩ
		V _{GS} = 10 V, I _D = 8 A		9.4	11.4	

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	- /	1350	1600	pF
Reverse transfer capacitance	C_{rss}	((// \) \ \	-(63	96	
Output capacitance	C _{oss}		7	240) —	
Gate resistance	r _g	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 5 \text{ MHz}$	1.0	14	2.1	Ω
Switching time (rise time)	t _r	See Fig. 6.2.1.		2.2		ns
Switching time (turn-on time)	t _{on}		//-//	8.2		
Switching time (fall time)	t _f			2.3	_	
Switching time (turn-off time)	t _{off}		// –	17	_	

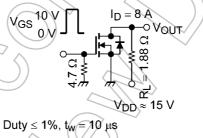


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	Q_g	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 16 \text{ A}$	-	20	1	nC
gate-drain)		$V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 16 \text{ A}$		9.9		
Gate-source charge 1	Q _{gs1}	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 16 \text{ A}$	_	4.4		
Gate-drain charge	Q_{gd}		_	2.1	_	
Gate switch charge	Q _{SW}		_	4.3		

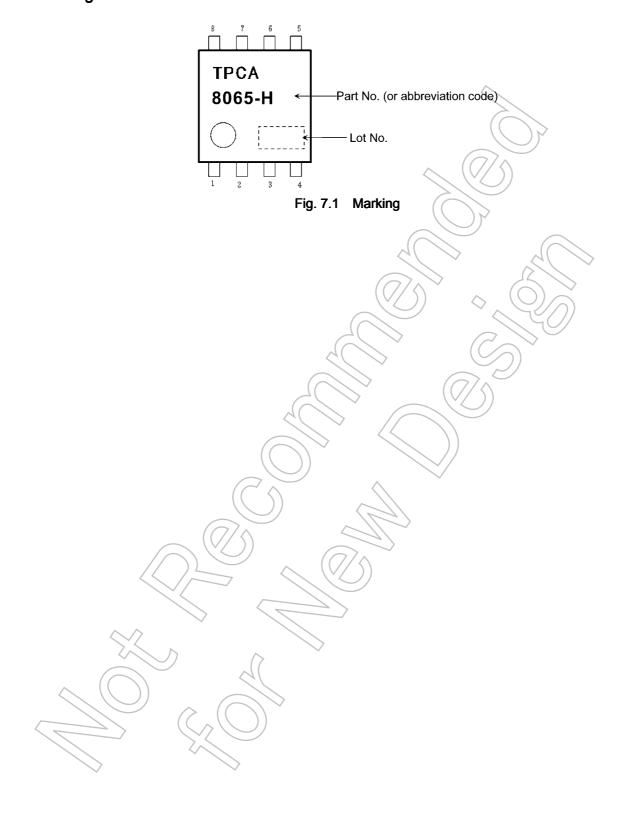
6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed)	(Note 5)	I _{DRP}	_	_	_	48	Α
Diode forward voltage	·	V_{DSF}	I _{DR} = 16 A, V _{GS} = 0 V	_	_	-1.2	V

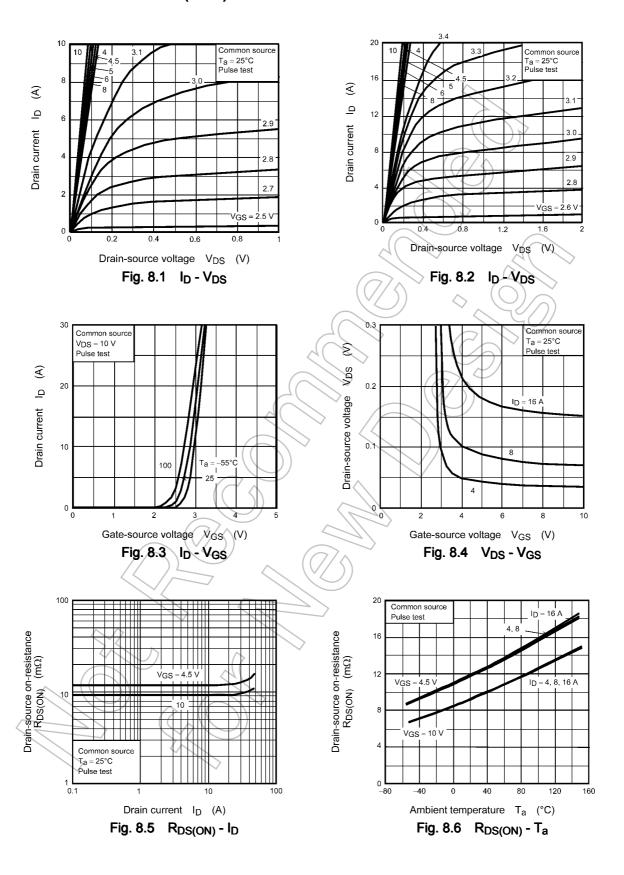
Note 5: Ensure that the channel temperature does not exceed 150 $^{\circ}\text{C}$.



7. Marking



8. Characteristics Curves (Note)



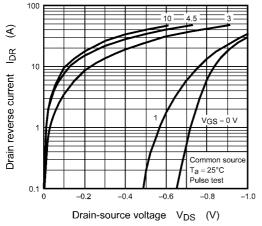


Fig. 8.7 IDR - VDS

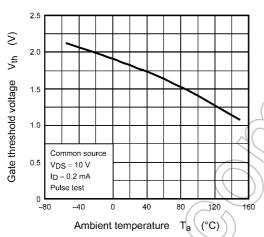


Fig. 8.9 V_{th} - T_a

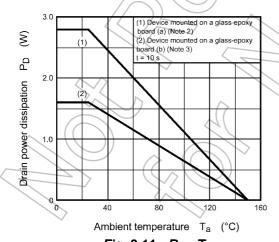


Fig. 8.11 P_D - T_a (Guaranteed Maximum)

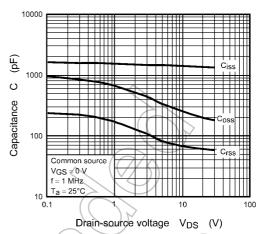


Fig. 8.8 Capacitance - VDS

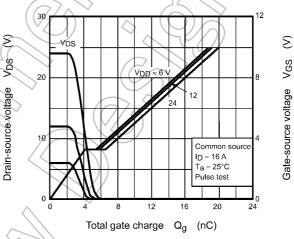


Fig. 8.10 Dynamic Input/Output Characteristics

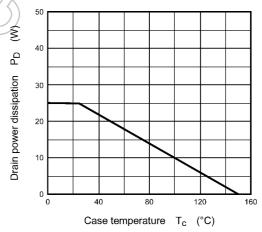


Fig. 8.12 P_D - T_c (Guaranteed Maximum)

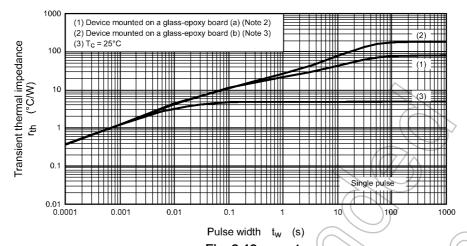


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

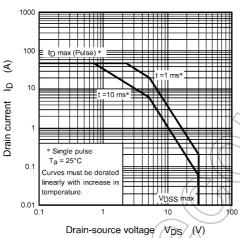


Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

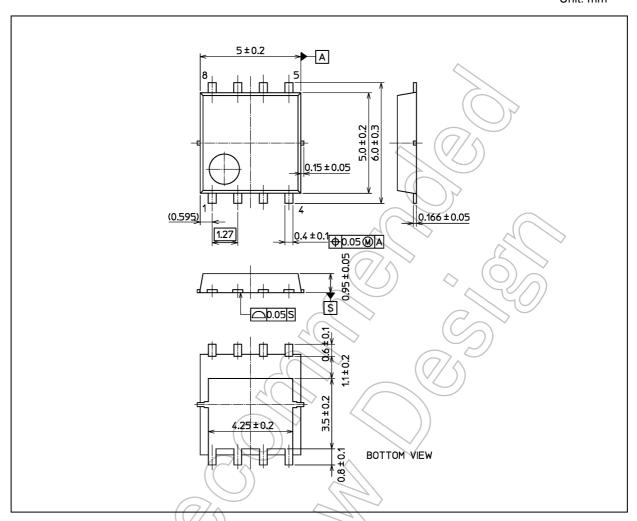
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

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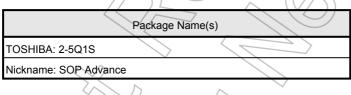


Package Dimensions

Unit: mm



Weight: 0.069 g (typ.)





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